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(54) Title: COMPOSITIONS AND METHODS FOR DRYING PATTERNED WAFERS DURING MANUFACTURE OF INTEGRATED CIRCUITRY PRODUCTS

(57) Abstract: Drying of patterned wafers is achieved in a manner effecting removal of water from the patterned wafers without collapse or deterioration of the pattern structures thereof. The drying is carried out in one aspect of the invention with a composition containing supercritical fluid, and at least one water-reactive agent that chemically reacts with water to form reaction product(s) more soluble in the supercritical fluid than water. Various methodologies are described for use of supercritical fluids to dry patterned wafers, which avoid the (low water solubility) deficiency of supercritical fluids such as supercritical CO2.